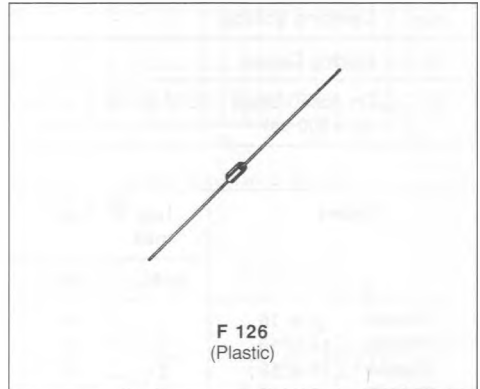


- BIDIRECTIONAL DEVICE USED TO **TELEPHONE PROTECTION**
- CHARACTERISTIC OF STAND-OFF AND BREAKDOWN VOLTAGE SIMILAR TO A TRANSIL (V_{off})
- HIGH FLOWOUT CAPABILITY BECAUSE OF ITS BREAKOVER CHARACTERISTIC (V_{on})


ABSOLUTE RATINGS (limiting values) ($T_J = 25\text{ }^\circ\text{C}$ - $L = 10\text{ mm}$)

Symbol	Parameter		Value	Unit
P	Power Dissipation on Infinite Heatsink	$T_{amb} = 50\text{ }^\circ\text{C}$	1.7	W
I_{pp}	Peak Pulse Current	1 ms expo	50	A
		8-20 μs expo	100	
I_{TSM}	Non Repetitive Surge Peak on-state Current	$t_p = 20\text{ ms}$	30	A
di/dt	Critical Rate of Rise of on-state Current	Non Repetitive	100	A/ μs
dv/dt	Critical Rate of Rise of off-state Voltage	67 % $V_{(BR)}$ min	5	kV/ μs
T_{stg} T_J	Storage and Operating Junction Temperature Range		- 40 to 150	$^\circ\text{C}$
			150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering During 10 s at 4 mm from Case		230	$^\circ\text{C}$

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-l)}$	Junction-leads on Infinite Heatsink	$L = 10\text{ mm}$	60	$^\circ\text{C/W}$
$R_{th(j-a)}$	Junction-ambient on Printed Circuit		100	$^\circ\text{C/W}$

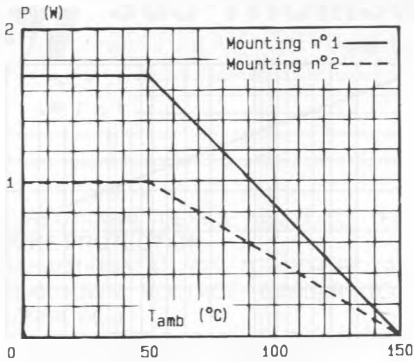


Fig.1 - Power dissipation versus ambient temperature.

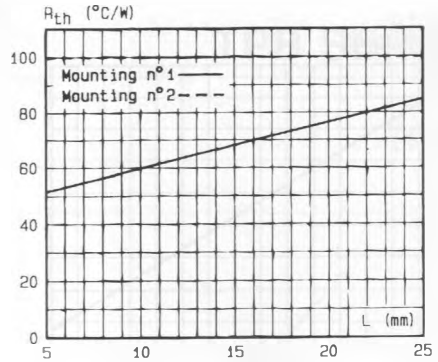


Fig.2 - Thermal resistance versus lead length.

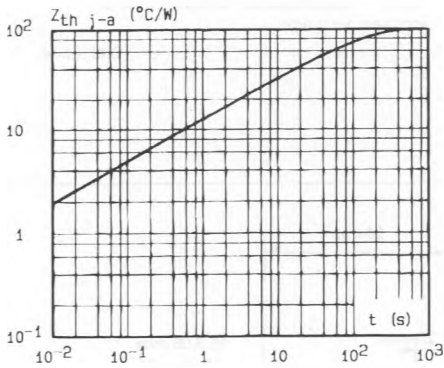


Fig.3 - Transient thermal impedance junction-ambient for mounting n°2 versus pulse duration (L = 10 mm).

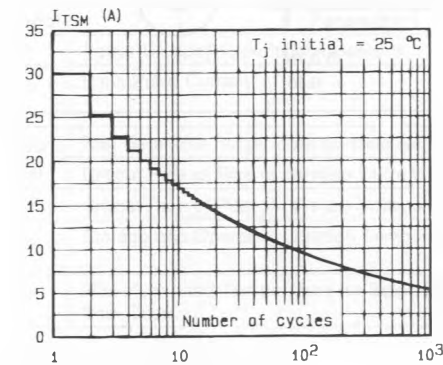
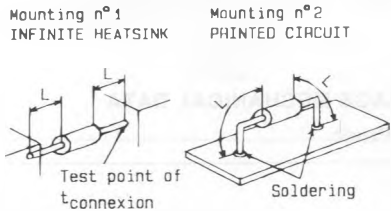


Fig.4 - Non repetitive surge peak on-state current versus number of cycles.

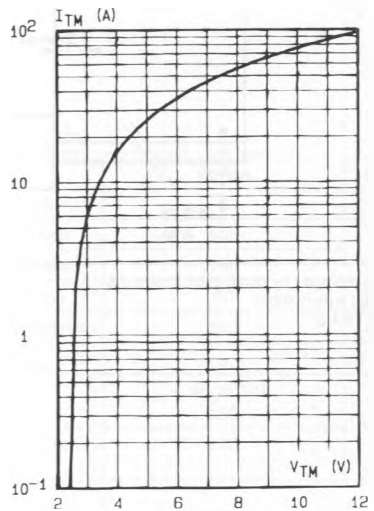


Fig.5 - Peak forward current versus peak forward voltage drop (typical values).

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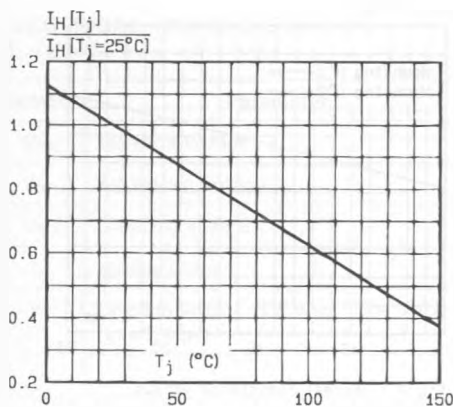


Fig.6 - Relative variation of holding current versus junction temperature.

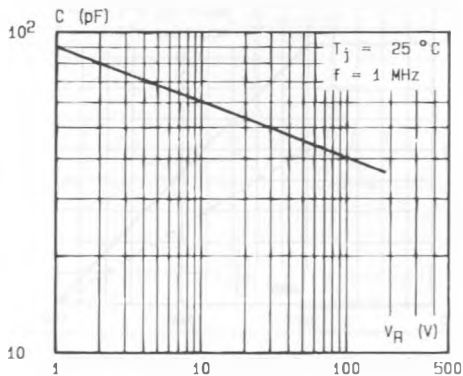
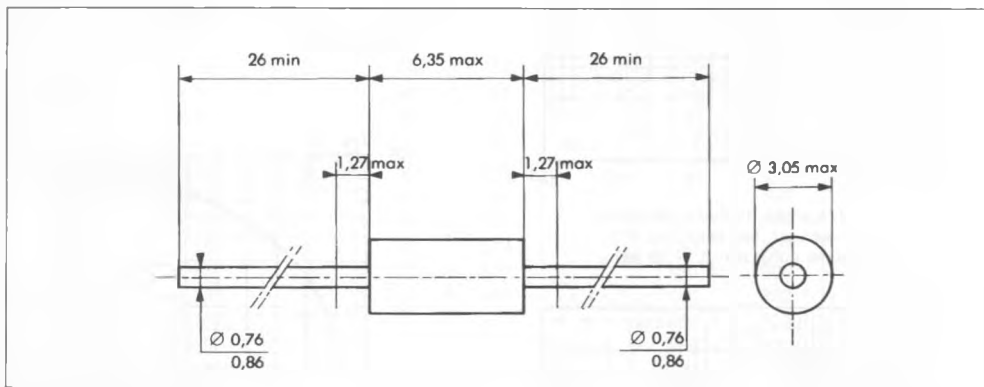


Fig.7 - Capacitance versus reverse applied voltage.

DB8TPA4

PACKAGE MECHANICAL DATA

F 126 Plastic



Cooling method : by conduction (method A)

Marking : type number

Weight : 0.4 g